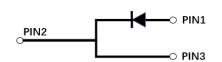




Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	7A
Qc	27nC





Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

• Package: TO-252

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112005DG1
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge peak) @ T _i =25°C	V_{RSM}	٧	1200
Reverse voltage (DC) @ T _j =25°C	V_{DC}	V	1200
Continuous forward current @ T _C =25°C		А	14.8
Continuous forward current @ T _C =135°C	I _F		7
Continuous forward current @ T _C =153°C			5
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	50
Power Dissipation@ T _C =25°C	В	w	71
Power Dissipation@ T _C =110°C	Ртот		31
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	12.5
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175



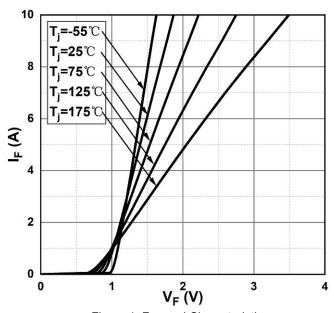


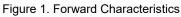
■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Famuerd voltage drap	M	V	I _F =5A, T _j =25°C	1.41	1.6
Forward voltage drop	V _F	V	I _F =5A, T _j =175°C	2.1	-
Povorco logicado gurrent		μА	V _R =1200V, T _j =25°C	0.5	16
Reverse leakage current	I _R		V _R =1200V, T _j =175°C	8	-
Total capacitive charge	Q _C	nC	$V_R=800V, T_j=25^{\circ}C, Q_C=\int_0^{VR}C(V)dV$	27	-
Total capacitance C		pF	V _R =0V, f=1MHZ	377	-
	С		V _R =400V, f=1MHZ	25	-
			V _R =800V, f=1MHZ	19	-
Capacitance Stored Energy	Ec	μJ	V _R =800V	6.8	-

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J\text{-C}}$	°C W	2.1

■Typical Characteristics





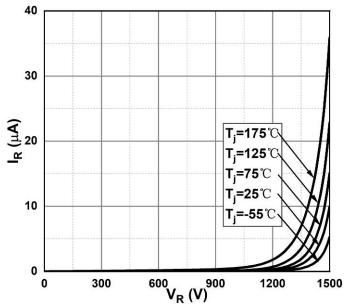
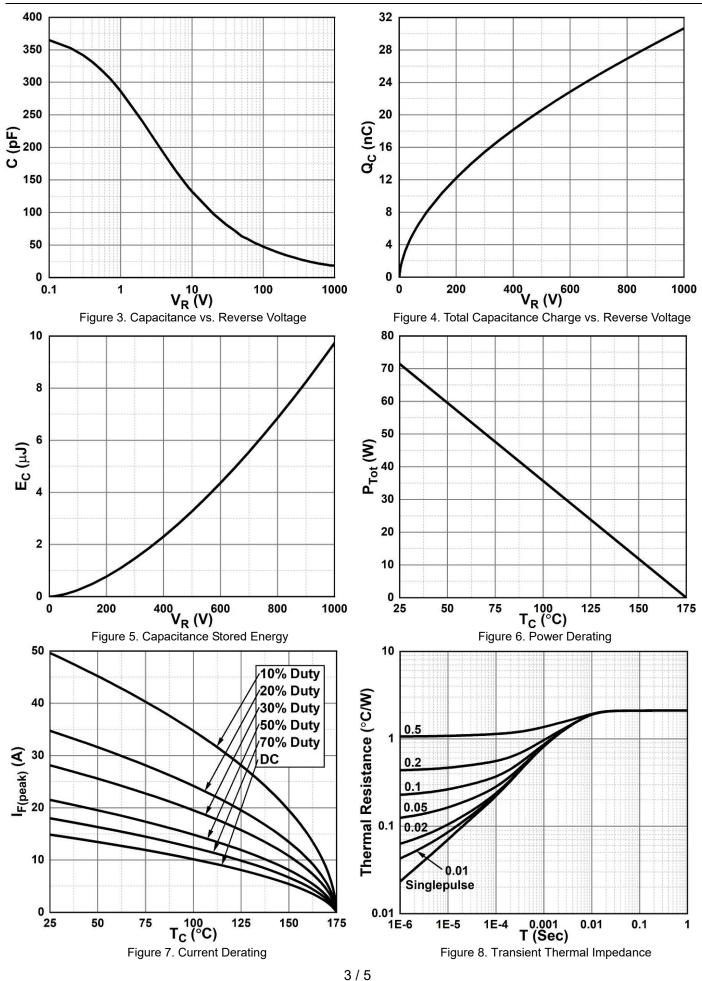


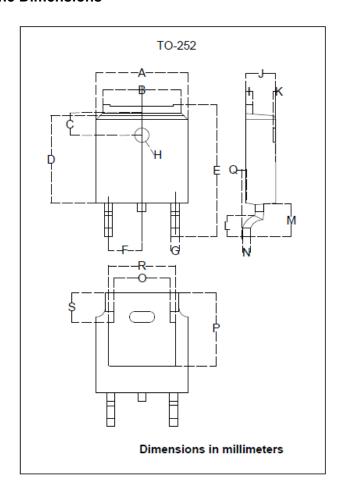
Figure 2. Reverse Characteristics





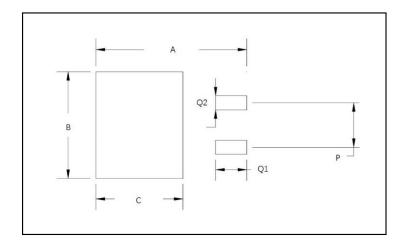


■ Outline Dimensions



TO-252		
Dim	Min	Max
Α	6.500	6.700
В	5.100	5.460
С	1.400	1.800
D	6.000	6.200
Е	10.000	10.400
F	2.166	2.366
G	0.660	0.860
Н	Ф1.050	Ф1.350
I	0.460	0.580
J	2.200	2.400
K	0	0.300
L	0.890	2.290
М	2.730	3.080
N	0.430	0.580
0	4.20	4.95
Р	5.15	5.45
Q	0	0.2
R	4.50	5.10
S	1.60	2.40

■ Suggested Pad Layout



Dim	Millimeters
Α	11.4
В	6.74
С	6.23
Р	4.56
Q1	2.28
Q2	1.52



YJD112005DG1



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